IN THE CLAIMS

1. (Currently Amended) A high frequency dielectric ceramics composition constituted by combining $(Zn_{1-x}M_x)TiO_3$ and $yTiO_2$ satisfies the conditions of:

M is Mg, Co or Ni, 'x' is [0≤x≤0.6] $0 < x \leq 0.6$ in case of Mg and 'x' is [0≤x≤1] $0 < x \leq 1$ in case of Co, and [0≤x≤1] $0 < x \leq 1$ in case of Ni, and [0≤y≤0.8] $0 < y \leq 0.8$.

2. (Original) A high frequency dielectric ceramics composition preparation method in which material powder of ZnO, MO (in this respect, MO is MgO, CoO or NiO) and TiO_2 is weighed according to a composition range of $(Zn_{1-x}M_x)TiO_3$ and $yTiO_2$ (M is one of Mg, Co and Ni, x is 0≤x≤0.6 in case of Mg, x is 0≤x≤1 in case of Co, x is 0≤x≤1 in case of Ni, and y is 0≤y≤0.8), mixed and dried,

calcined at a temperature of 850~950°C,

the calcined powder is crushed,

the crushed power is shaped,

the shaped body is fired at a temperature of 925~1100°C, and

$(Zn_{1-x}M_x)TiO_3$ is calcined at a temperature corresponding to a region (region II) of below a phase dissociation temperature as shown in Figure 2 to obtain $(Zn_{1-x}M_x)TiO_3$ (M is Mg, Co or Ni) of a single phase of rhombohedral/hexagonal crystal.

3. (Original) The method of claim 2, wherein the shaped body is made in a manner that an aqueous solution adding a PVA binder is sprayed onto the crushed powder to make a granule, to which a pressure is applied.

4. (Original) The method of claim 3, further comprises a step for maintaining the shaped body at a temperature of 300~500°C for a predetermined time and removing the binder.

5. (Original) The method of claim 2, wherein $(Zn_{1-x}M_x)TiO_3$ is first calcined and $yTiO_2$ ($0 \leq y \leq 0.8$) is added to $(Zn_{1-x}M_x)TiO_3$ and then sintered.

6. (Original) The method of claim 2, wherein $(Zn_{1-x}M_x)TiO_3$ and $yTiO_2$ are sintered at the same time and sintered.

7. (Original) The method of claim 2, wherein TiO2 is anatase or rutile.

8. (Original) A high frequency dielectric ceramics composition constituted from combination of $(Zn_{1-a}Mg_{1-b}Co_{1-c}Ni_{1-d})TiO_3$ and $yTiO_2$ ($0 \leq a \leq 1$, $0 \leq b \leq 1$, $0 \leq c \leq 1$, $0 \leq d \leq 1$), and $0 \leq y \leq 0.8$.

9. (Currently Amended) ~~Various high frequency devices such as a stacked chip capacitor, a stacked chip filter, a stacked chip capacitor/inductor composite device and a module, a low temperature sintered substrate, a resonator and a filter or a ceramic antenna, are fabricated by using the dielectric~~ High frequency devices comprising the composition of claim 1.

10. (New) The high frequency devices of claim 9, wherein the high frequency devices are selected from the group consisting of a stacked chip capacitor, a stacked chip filter, a stacked chip capacitor/inductor composite device and a module, a low-temperature sintered substrate, a resonator, a filter, a ceramic antenna and combinations thereof.